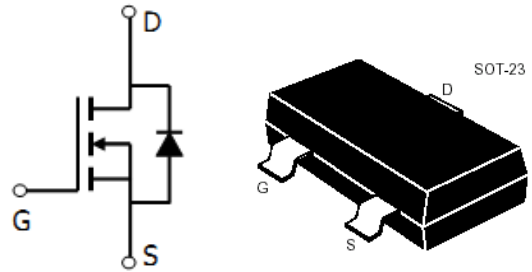


N-Channel Enhancement-Mode MOSFETs

■ MAXIMUM RATINGS

Characteristic	Symbol	Max	Unit
Drain-Source Voltage	BV_{DSS}	20	V
Gate- Source Voltage	V_{GS}	± 8	V
Drain Current (continuous)	I_D	4.2	A
Drain Current (pulsed)	I_{DM}	16	A
Total Device Dissipation $T_A=25^\circ\text{C}$	P_D	1200	mW
Junction	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55to+150	$^\circ\text{C}$

■ DEVICE MARKING
SL3414A=A14

■ ELECTRICAL CHARACTERISTICS

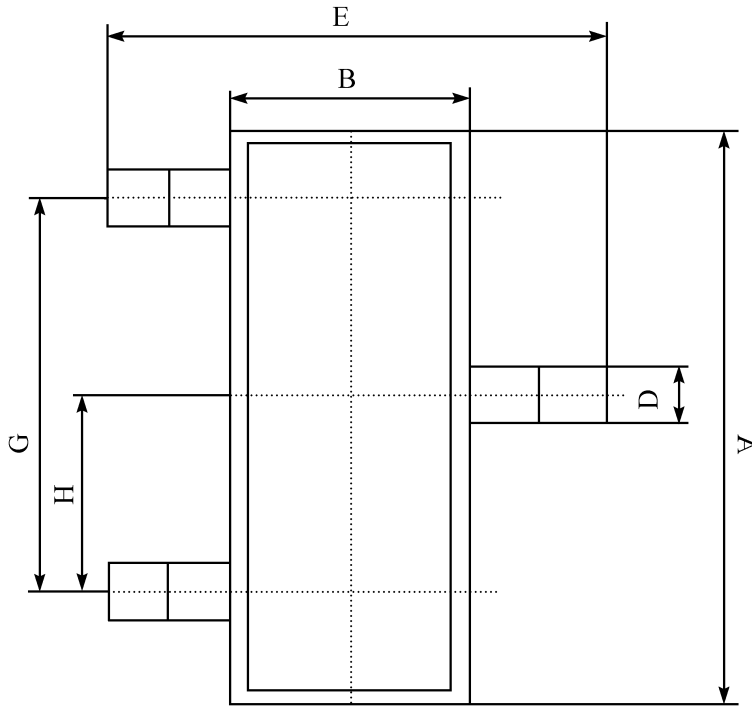
 (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage (I _D = 250uA, V _{GS} =0V)	BV _{DSS}	20	—	—	V
Gate Threshold Voltage (I _D = 250uA, V _{GS} = V _{DS})	V _{GS(th)}	0.4	0.6	1	V
Diode Forward Voltage Drop (I _S = 1A, V _{GS} =0V)	V _{SD}	—	—	1	V
Zero Gate Voltage Drain Current (V _{GS} =0V, V _{DS} = 16V) (V _{GS} =0V, V _{DS} = 16V, T _A =55°C)	I _{DSS}	—	—	1 5	uA
Gate Body Leakage (V _{GS} =±8V, V _{DS} =0V)	I _{GSS}	—	—	±100	nA
Static Drain-Source On-State Resistance (I _D =4.2A, V _{GS} =4.5V) (I _D =3.7A, V _{GS} =2.5V) (I _D =3.2A, V _{GS} =1.8V)	R _{DS(ON)}	—	41 52 67	50 63 87	mΩ
Input Capacitance (V _{GS} =0V, V _{DS} = 10V, f=1MHz)	C _{ISS}	—	436	—	pF
Common Source Output Capacitance (V _{GS} =0V, V _{DS} = 10V, f=1MHz)	C _{OSS}	—	66	—	pF
Turn-ON Time (V _{DS} = 10V, V _{GS} =5V, R _{GEN} =6Ω)	t _(on)	—	5.5	—	ns
Turn-OFF Time (V _{DS} = 10V, V _{GS} =5V, R _{GEN} =6Ω)	t _(off)	—	40	—	ns

Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%

■DIMENSION

(UNIT): mm



序號	數值及公差
A	2.90±0.10
B	1.30±0.10
C	1.00±0.10
D	0.40±0.10
E	2.40±0.20
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.2
N	0.60±0.10
P	7±2°

